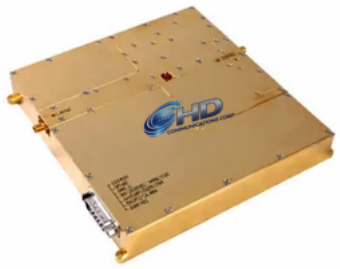
HD30503
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

High Power Linear chip & wire GaAsFET design
Instantaneous ultra-wide Bandwidth
Suitable for all single channel modulation standards
Suitable for C, X and Ku band applications
Built-in protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	6.0 - 18.0 GHz	
Power Output Psat	20 Watt Min	CW
Small Signal Gain	43 dB Min	
Power Gain Flatness	4.0 dB p-p Ma	
Input Return Loss	-10 dB Max	
Harmonics	-15 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Noise Figure	10 dB Max	
Operating Voltage	12 VDC Nom	
Current Consumption	22 Amp Typ	At rated Pout
Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	170 x 180 x 27 mm	Excluding connectors
Weight	1.75 kg	
RF Connectors In/Out	SMA female	Cover Flange
DC Power / Interface Connector	7-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

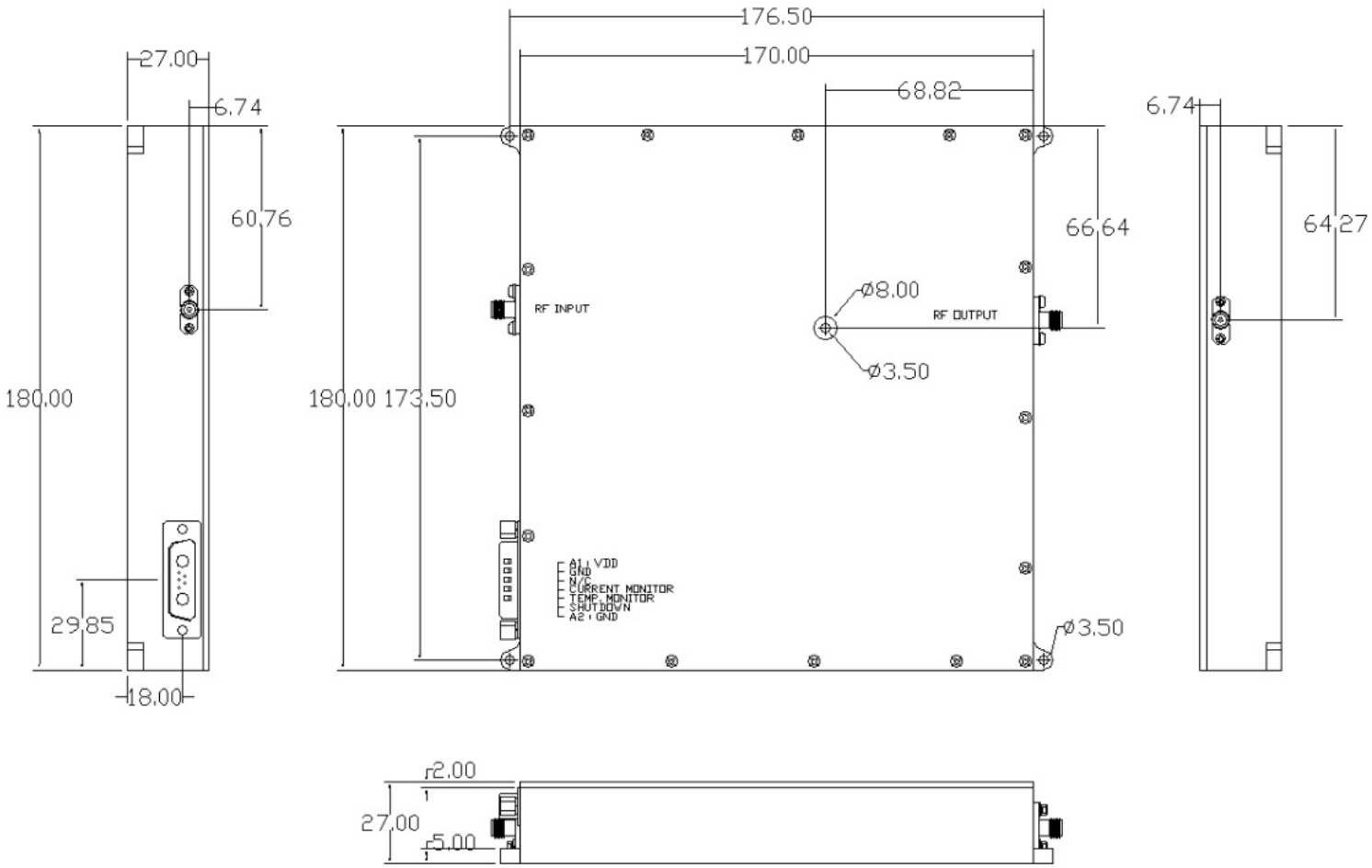
D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	GND	Ground
2	N/A	N/A
3	CURRENT SENSOR	I_D@20mV/100mA Typ
4	TEMP SENSOR	V_T@10mV/°C + 500mV Typ
5	SHUTDOWN	Enable = TTL "Hi" or open / Disable = TTL "Lo" or short
A1	VDD	12VDC
A2	GND	Ground

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Specifications subject to change without notice. Specifications and drawings may vary with selected options.

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OUTLINE DRAWING



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